

IN THE SPECIFICATION:

Replace the paragraph beginning at page 1, line 5, with:

The present invention relates to a method for manufacturing a semiconductor device and the semiconductor device manufactured by the method, in which the semiconductor device is manufactured by laser cutting a plate having a number of such semiconductor devices.

Replace to the paragraph beginning at page 1, line 19, with:

PCT/WO98/13862 discloses a method for manufacturing a GaAs high power semiconductor device having such heat radiation metal layer, which is illustrated in Figs. 5A to 5L. According to the method, as shown in Fig. 5A, a first main surface of GaAs substrate 31 carrying semiconductor elements is etched to form a first separation groove 33, in which a photoresist layer 32 provided on the first main surface is used as a mask. Then, as shown in Fig. 5B, the first separation groove 33 is plated with a first metal layer 34. As shown in Fig. 5C, the GaAs substrate 31 then has wax 35 applied on the first main surface and is further bonded onto a supporting wafer 36 made of glass or sapphire. Also, the GaAs substrate 31 is polished at its second main surface to reduce its thickness to about 20 to 30 μ m. Subsequently, as shown in Fig. 5D, the GaAs substrate 31 is provided at its second main surface with a photoresist layer 44 which is then patterned with an aperture opposing the first separation groove 33. The photoresist layer 44 so patterned is used as a mask for an etching in which the second main surface of the GaAs substrate 31 is etched to the extent that the bottom surface of the first metal layer 34 in the first separation groove 33 is exposed, which results in a second separation groove 63 shown in Fig. 5E.

Replace the paragraph beginning at page 2, line 18, with:

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a³

Replace the paragraph beginning at page 9, line 22, with:

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a4

Replace the paragraphs beginning at page 9, line 25, with:

Figs. 2A and 2B show manufacturing processes for the semiconductor device according to the first embodiment of the present invention;

Figs. 3A-3C show manufacturing processes for the semiconductor device according to the second embodiment of the present invention;

Fig. 4 shows a manufacturing process for the semiconductor device according to the second embodiment of the present invention; and

Figs. 5A-5L show manufacturing processes for the prior art semiconductor device.

Replace to the paragraph beginning at page 10, line 24, with:

Referring to Figs. 1A to 2B, a method for manufacturing a semiconductor device and a semiconductor device manufactured by the method according to the present invention will be described hereinafter.

Replace the paragraph beginning at page 11, line 3, with:

According to the method, as best shown in Fig. 1A, provided is a GaAs substrate 1 having a semiconductor element in its first main surface. The GaAs substrate 1 is provided on the first main surface with a photoresist layer 2. The layer 2 is used as a mask in a subsequent wet etching process in which the GaAs substrate 1 is etched to form a first separation groove (a surface separation 10 groove) 1a. Then, a catalyst layer 3 including palladium (Pd) is deposited on an entire surface of the remaining photoresist layer 2 by a suitable film forming technique such as evaporation and sputtering deposition. In this film formation, a part of the catalyst layer 3 is formed on a surface of the first separation groove 1a.

[Replace the paragraph beginning at page 11, line 16, with]

The palladium included in the catalyst layer 3 exists in a considerably stable state so that it never elutes from the catalyst layer 3 to result in an unwanted separation of the catalyst layer 3 in a subsequent formation of the second separation layer 1b (see Fig. 1I), which would otherwise be caused if the eluted palladium forms an oxide between the catalyst layer 3 and the GaAs substrate 1.

[Replace the paragraph beginning at page 11, line 24, with:]

It should be noted that the possible separation of the catalyst layer 3 will result in an unevenness in thickness of a metal layer 10 to be formed on the bottom surface of the catalyst layer 3 and then cut by an exposure to laser light. Also, the unevenness can make defects in the laser cutting in a separation process of the semiconductor devices (see Fig. 1K), which decreases the yield of the semiconductor device. Contrary to this, the catalyst layer 3 so formed will increase the yield of the device.

[Replace the paragraph beginning at page 12, line 8, with:]

Referring next to Fig. 1B, the catalyst layer 3 on the photoresist layer 2 is removed using a lift off method, except in the first separation groove 1a.

[Replace the paragraph beginning at page 12, line 12, with:]

It should be noted that the catalyst layer 3 is a single layer made of palladium, having a thickness of about 10 nm. Preferably, the thickness of the palladium layer is in the range of about 5 to 30 nm. Alternatively, the catalyst layer 3 may be made from layers of palladium and titanium. In this instance, the palladium layer should overlie the titanium layer so that the catalyst layer 3 serves as a catalyst.

[Replace the paragraph beginning at page 12, line 20, with:]

Referring next to Fig. 1C, a photoresist layer 22 is formed on the substrate 1 so that it does not cover the first separation groove 1a. As can be seen from the drawing, edges of the photoresist layer 22 extend slightly into the first separation groove 1a, so that slanted side surfaces defining a part of the first separation groove 1a are half (about 50%) covered by the photoresist 22.

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formed on the second main surface or the peripheral surface of the GaAs substrate 1. This means that, by using this method, the nickel based plating layer 4 can be formed selectively only near the catalyst layer 3 to which the atomic hydrogen can be supplied. This, in turn, allows that the topmost of the nickel based plating layer 4 to be located below that of the opening of the first separation groove 1a, which ensures that no short circuit would occur between the plating layer 4 and the bonding wire at the wirebonding of the GaAs substrate 1.

[Replace the paragraph beginning at page 15, line 4, with:]

Furthermore, although the nickel based plating layer 4 is formed using the catalyst layer 3, it may be provided only by electroless plating. In this instance, the GaAs substrate 1 must be dipped in a solution containing phosphorus before the electroless plating in order to form a catalyst nucleus in the first separation groove 1a. This plating may have some drawbacks.

[Replace the paragraph beginning at page 15, line 11, with:]

Specifically, phosphorus ion may deposit on a portion on which the nickel based plating layer should not be formed, for example, the upper surface of the photoresist layer and the second main surface of the GaAs substrate 1. This undesired deposition may result in the nickel based plating layer being formed on the second main surface of the GaAs substrate 1 in the electroless plating.

[Replace the paragraph beginning at page 15, line 18, with:]

Also, the nickel based plating layer grown on the photoresist layer disadvantageously may in part separate into a solvent in a process for removing the photoresist (see Fig. 1E), so the separated plating layer adheres again to the surface of the GaAs substrate 1 in the subsequent processes, which provides an adverse effect.

Replace the paragraph beginning at page 15, line 25, with:

Further, the nickel based plating layer formed on the second main surface of the GaAs substrate 1 may result in a variation of the etching of the second main surface of the GaAs substrate 1 in a thinning process of the GaAs substrate 1 (Fig. 1F), causing an unevenness in thickness of the etched GaAs substrate 1. In addition, the nickel based plating layer formed on the peripheral surface of the GaAs substrate 1 may result in binding in a polishing blade at the thinning process, which may crack or damage the GaAs substrate.

Replace the paragraph beginning at page 16, line 12, with:

Next, as shown in Fig. 1F, the first main surface of the GaAs substrate 1 is coated with a wax 5 as an adhesive through which a supporting wafer 6 is bonded on the substrate 1. The supporting wafer 6 is a plate made of suitable material such as glass and sapphire. Then, the GaAs substrate 1 is thinned from its second main surface to about 20 to 30 μ m. The thinning may be accomplished by any suitable manner such as grinding, lapping, and polishing.

Replace the paragraph beginning at page 16, line 20, with:

Next, as shown in Fig. 1G, the entire second main surface of the GaAs substrate 1 is coated with a first conducting layer 7. The conducting layer 7 may be formed by, for example, forming a nickel based plating layer on the first main surface of the GaAs substrate 1, and substituting the upper surface of the plating layer for gold (Au). Then, a part of the second main surface of the GaAs substrate 1, opposing the first separation groove 1a, is formed with a photoresist layer (not shown). Preferably, a width of the photoresist layer is smaller than that of the groove 1a. The photoresist layer is used as a mask in an electrolytic process in which a PHS layer 8 made from gold is formed on the conducting layer 7. Then, the photoresist layer is removed.

[Replace the paragraph beginning at page 17, line 9, with:]

As shown in Fig. 1H, the PHS layer 8 serves as a mask in an etching process in which a portion of the conducting layer 7 adjacent to the groove 1a is removed. This etching process is extended to the lower surface of the catalyst layer 3 to form a second separation groove 1b.

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[Replace the paragraph beginning at page 17, line 14, with:]

Next, as shown in Fig. 1I, a second conducting layer 9 is formed on surfaces of the second separation groove 1b and the PHS layer 8 by electroless plating, similar to the first conducting layer 7. The process for forming the second conducting layer 9 may be the same as that for the first conducting layer 7. Further, a metal layer 10 is formed on the second conducting layer 9 by the electroplating process. Preferably, the metal layer 10 is made of a metal having a melting point higher than that of the nickel based plating layer 4 in the first separation groove 1a and having a reflection ratio of less than 8% of YAG laser light. Also preferably, the nickel based plating layer 4 is made from nickel based alloy selected from materials such as Ni-P, Ni-B and Ni-B-W, and the metal layer 10 is made of material such as nickel and chromium.

[Replace the paragraph beginning at page 18, line 4, with:]

Referring to Fig. 1J, the entire surfaces of the metal layer 10 and the second separation groove 1b are covered by a titanium (Ti) layer about 0.05 μ m in thickness and then a gold (Au) layer about 0.2-0.3 μ m in thickness by a suitable film formation technique, such as sputtering deposition and evaporation, forming a Ti/Au layer 11.

[Replace the paragraph beginning at page 18, line 10, with:]

It should be noted that the Ti/Au layer 11, which improves wettability of the lower surface of the PHS layer 8 against an AuSn solder used for bonding the lower surface of the PHS layer 8 onto the package, can be removed therefrom.

Replace the paragraph beginning at page 18, line 15, with:

Finally, referring to Fig. 1K, the GaAs substrate 1 is removed from the supporting wafer 6. Also, the wax 5 is removed using an organic solvent. Further, an expandable film (not shown) is attached on the PHS layer 8 on the second main surface (back side) of the GaAs substrate 1. Then, the YAG laser beam is irradiated from above, toward the first separation groove 1a to heat-cut the nickel based plating layer 4, the catalyst layer 3, the second conducting layer 9 having the nickel plating layer and the gold layer, the metal layer 10, and the Ti/Au layer 11 (as shown by a dotted line in Fig. 1K). It should be noted that the expandable film remains uncut, and is expanded in all directions by a suitable expander to separate each element so manufactured from one another. In this way, the GaAs substrate 1 is separated into pieces, each of which forms an independent semiconductor element having the separated piece of the GaAs substrate 1. An example of the semiconductor element or device so manufactured is illustrated in Figs. 2A and 2B.

Replace the paragraph beginning at page 19, line 9, with:

In the semiconductor device so manufactured, the topmost of the nickel based plating layer (metal layer) 4, running around the GaAs substrate 1, is positioned below the first main surface of the GaAs substrate 1. Therefore, when a bonding wire is bonded on the first main surface of the GaAs substrate 1 as shown in Fig. 5L, it is never short circuited to the nickel based plating layer 4, which- increases the production yield of the semiconductor device.

Replace the paragraph beginning at page 19, line 18, with:

As best shown in Fig. 4B, the semiconductor device so manufactured has a peripheral projecting flange 20 running around the substrate 1. The flange includes a plurality of layers; the nickel based plating layer 4 (for example, a Ni-P layer, Ni-B layer, a NI-B-W layer), catalyst layer 3 (for example, a Pd layer, a Pd/Ti layer), nickel based electrolessly plated alloy layer (for example, the Ni-P layer, Ni-B layer, NI-B-W layer) ;

substituted electroless gold plated layer, laser-cut metal layer 10 (for example, a Ni layer, a Cr layer), gold layer or Ti/Au layer 11. It should be noted that the second conducting layer 9 has a nickel based electroless plating alloy layer and a 5 substituted electrolessly gold plated layer. It should also be noted that the gold layer or the Ti/Au layer 11 may be eliminated as described above.

[Replace the paragraph beginning at page 20, line 10, with:]

A second embodiment of the present invention will be described below with reference to Fig. 3A through Fig. 4. In this embodiment, processes described with reference to Figs. 1A to 1I in connection with the first embodiment are performed, thereby obtaining an intermediate product shown 15 in Fig 3A. The intermediate product is processed, which will be described below.

[Replace the paragraph beginning at page 20, line 17, with:]

Referring to Fig. 3B, the entire surface of metal layer 10 is coated with a positive photoresist layer which is then exposed and then developed so that only a part of the layer indicated at 222 remains in the second separation groove 1b. Then, a major part of the second conducting layer 9 and the metal layer 10 on the PHS layer 8 is removed by etching or milling, so that a minor part of the second conducting layer 9 and the laser-cut layer 10 still remains in the second separation groove 1b.

[Replace the paragraph beginning at page 21, line 1, with:]

Finally, as shown in Fig. 3C, the remaining photoresist layer 222 is removed using an organic solvent or the like. Then, as described in the first embodiment, the YAG laser light is irradiated from above toward the first separation groove 1a to cut the nickel based plating layer 4, the catalyst layer 3, the second conducting layer 9, the laser-cut metal layer 10, and then the Ti/Au layer 11. In this way, the GaAs substrate 1 is separated into pieces, each of which forms an independent semiconductor element or device having the